

# RF-U 2.5-2

H-Field Probe 30 MHz up to 3 GHz



## Short description

The RF-U 2.5-2 near-field probe is designed for the selective measurements of RF currents in conducting paths, component connectors, SMD components, and IC-pins. The probe head has a magnetically active gap with an approx. width of 0.5 mm. To use, the head should be positioned directly onto the measured object.

The RF-U 2.5-2 is a passive near-field probe that functions like the RF-U 5-2 probe, but is designed for SMD components (pins). The near-field probe is small and handy. It has a current attenuating sheath and its upper side is electrically shielded. It can be connected to a spectrum analyzer or an oscilloscope with a 50  $\Omega$  input. The H-field probe does not have an internal terminating resistance of 50  $\Omega$ .

The near-field probe can be used for RF injection in the context of a surface scan in according to IEC 62132-9. The maximum forward power [dBm] for this application is shown in the diagram below. The curve for the probe factor used to calculate the decoupled fields strength is available from our sales department. Please note that the probe must not be held in the hand during coupling, and the user must ensure appropriate shielding from the surrounding environment. Langer EMV-Technik GmbH assumes no liability for damage to persons or equipment resulting from improper handling during coupling.

## Technical parameters

Frequency range	30 MHz ... 3 GHz
Resolution	$\approx$ 0.5 mm
Probe head dimensions	$\varnothing \approx$ 4 mm
Connector - output	SMB, male, jack
Weight	15 g

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Frequency response [dB $\mu$ V] / [dB $\mu$ A/m]



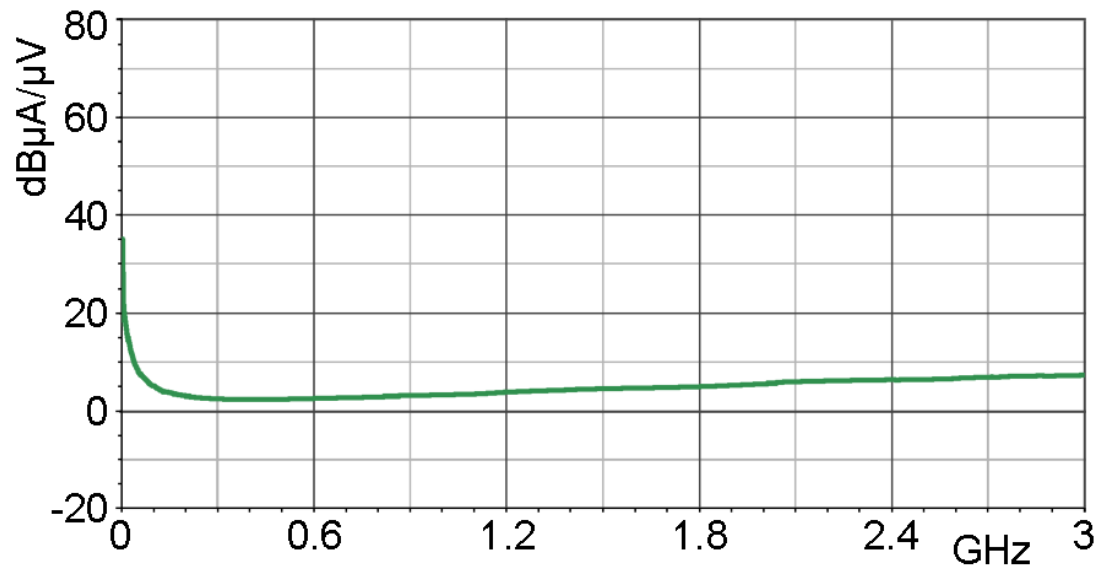
H-field correction curve [dB $\mu$ A/m] / [dB $\mu$ V]



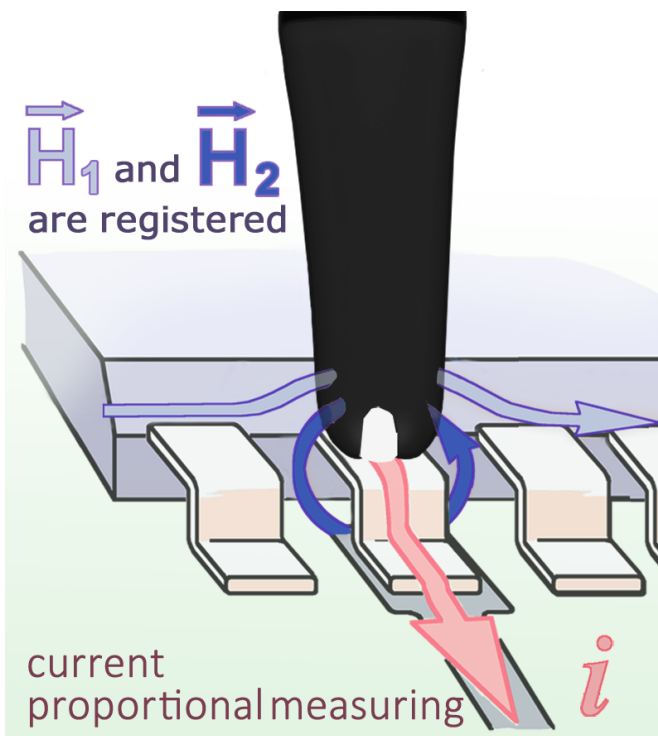
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Current correction curve [dB $\mu$ A] / [dB $\mu$ V]



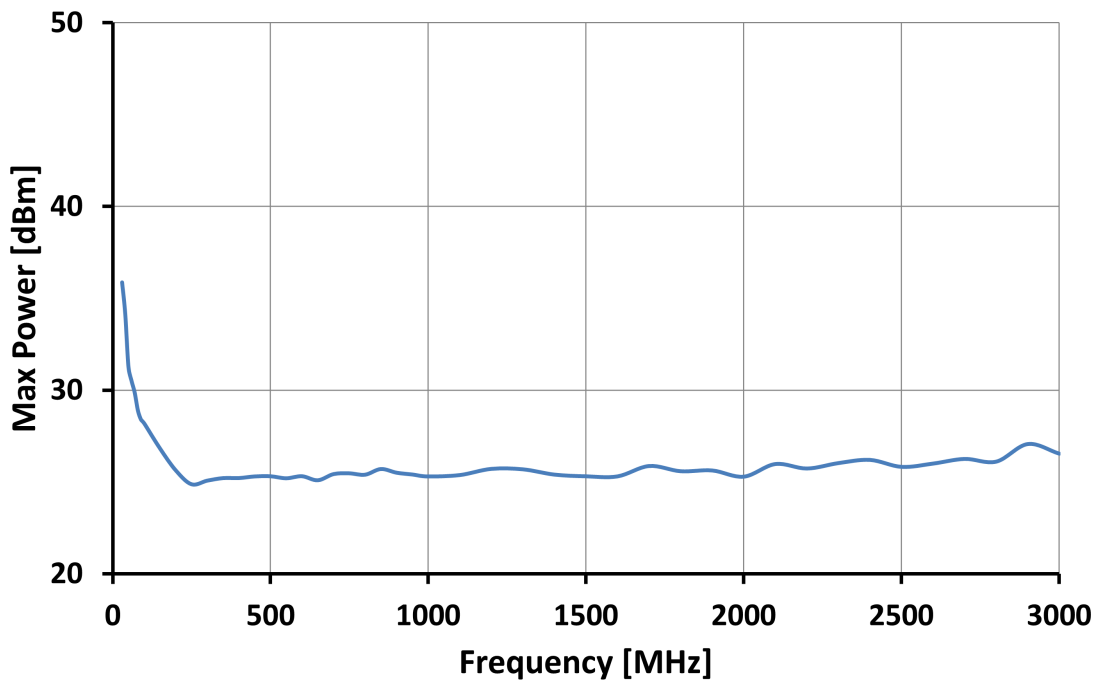
Measuring principles



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Max. Forward Power [dBm]



Probe head

